

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

2SK4085LS — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)= 0.33Ω (typ.)
- Input capacitance Ciss=1200pF (typ.)
- · 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

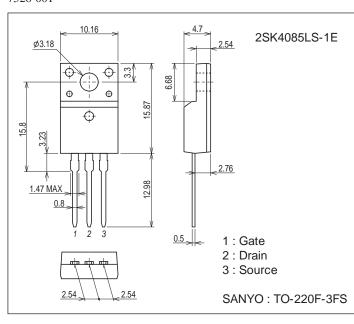
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		500	V
Gate-to-Source Voltage	VGSS		±30	V
D : 0 (D0)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	16	А
Drain Current (DC)	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	11	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	Α
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		141	mJ
Avalanche Current *5	I _{AV}		16	Α

^{*1} Shows chip capability.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Package Dimensions

unit : mm (typ) 7528-001



Product & Package Information

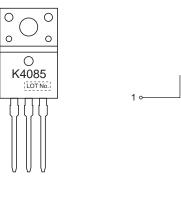
• Package : TO-220F-3FS

• JEITA, JEDEC : SC-67

• Minimum Packing Quantity: 50 pcs./magazine

Marking

Electrical Connection



SANYO Semiconductor Co., Ltd.

http://semicon.sanyo.com/en/network

^{*2} Package limited.

^{*3} SANYO's condition is radiation from backside.

^{*4} VDD=50V, L=1mH, IAV=16A (Fig.1)

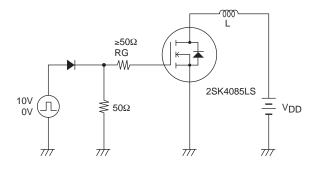
^{*5} L≤1mH, Single pulse

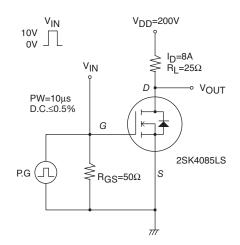
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Lloit	
Parameter	Symbol	Conditions	min.	typ.	max.	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	500			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =400V, V _{GS} =0V			100	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	3		5	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =8A	4.5	9		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =8A, V _G S=10V		0.33	0.43	Ω	
Input Capacitance	Ciss			1200		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		250		pF	
Reverse Transfer Capacitance	Crss			55		pF	
Turn-ON Delay Time	t _d (on)			26.5		ns	
Rise Time	t _r	See Fig 2		78		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		146		ns	
Fall Time	tf			57		ns	
Total Gate Charge	Qg			46.6		nC	
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =16A		8.2		nC	
Gate-to-Drain "Miller" Charge	Qgd			27.4		nC	
Diode Forward Voltage	V _{SD}	I _S =16A, V _{GS} =0V		0.95	1.3	V	

Fig.1 Avalanche Resistance Test Circuit

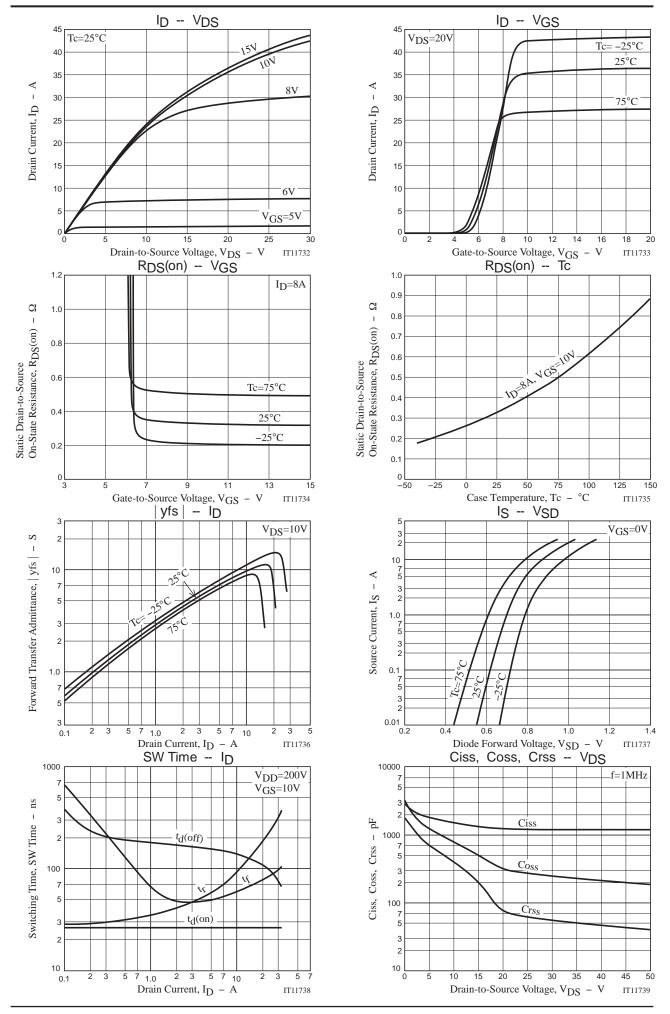
Fig.2 Switching Time Test Circuit

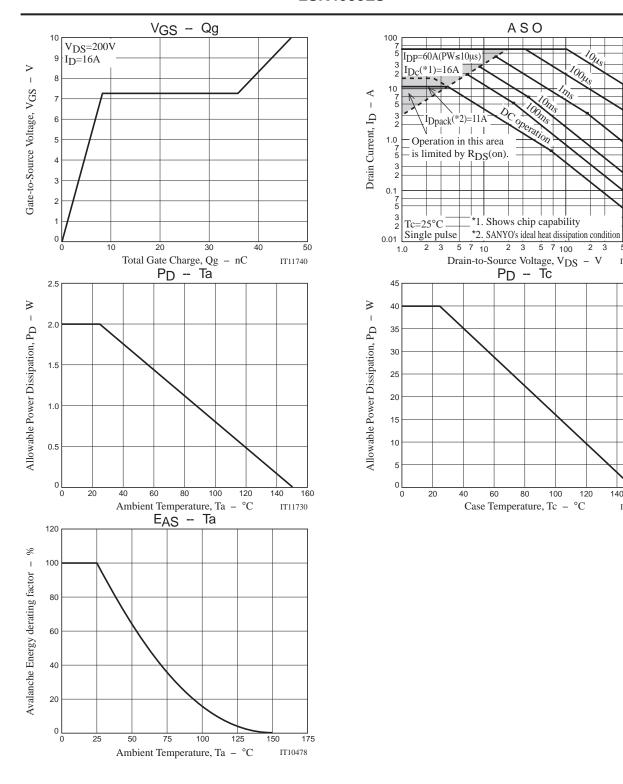




Ordering Information

Device	Package	Shipping	memo
2SK4085LS-1E	TO-220F-3FS	50pcs./magazine	Pb Free





IT16814

140

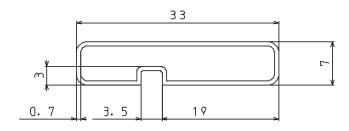
160

Magazine Specification

2SK4085LS-1E

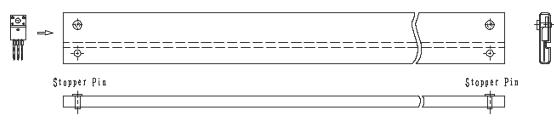
1. Packing Format

Package Name Magazine Name		Maximum Number of devices contained (pcs)			Packing format		
I a v a a g v T (a a a a	Iffre and two Identity		Inner box	Outer box	Inner BOX	Outer BOX	
TO-220F-3F\$	TO-220F	50	1, 000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dinensions:mm (external) 590×225×178	



Tolerance= ± 0 , 3mm Thickness=0, 7 ± 0 , 2mm Length =532, 5 ± 2 mm Material =PVC (Antistatic treatment)

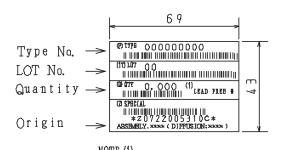
3. Storage method to magazine

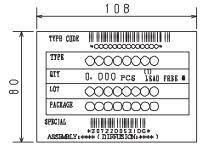


4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.





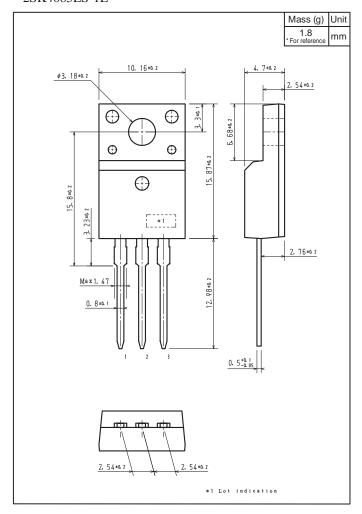
NOTE(1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase			
LEAD FREE	3	JEITA Phase 3A			

Outline Drawing

2SK4085LS-1E



Note on usage: Since the 2SK4085LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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